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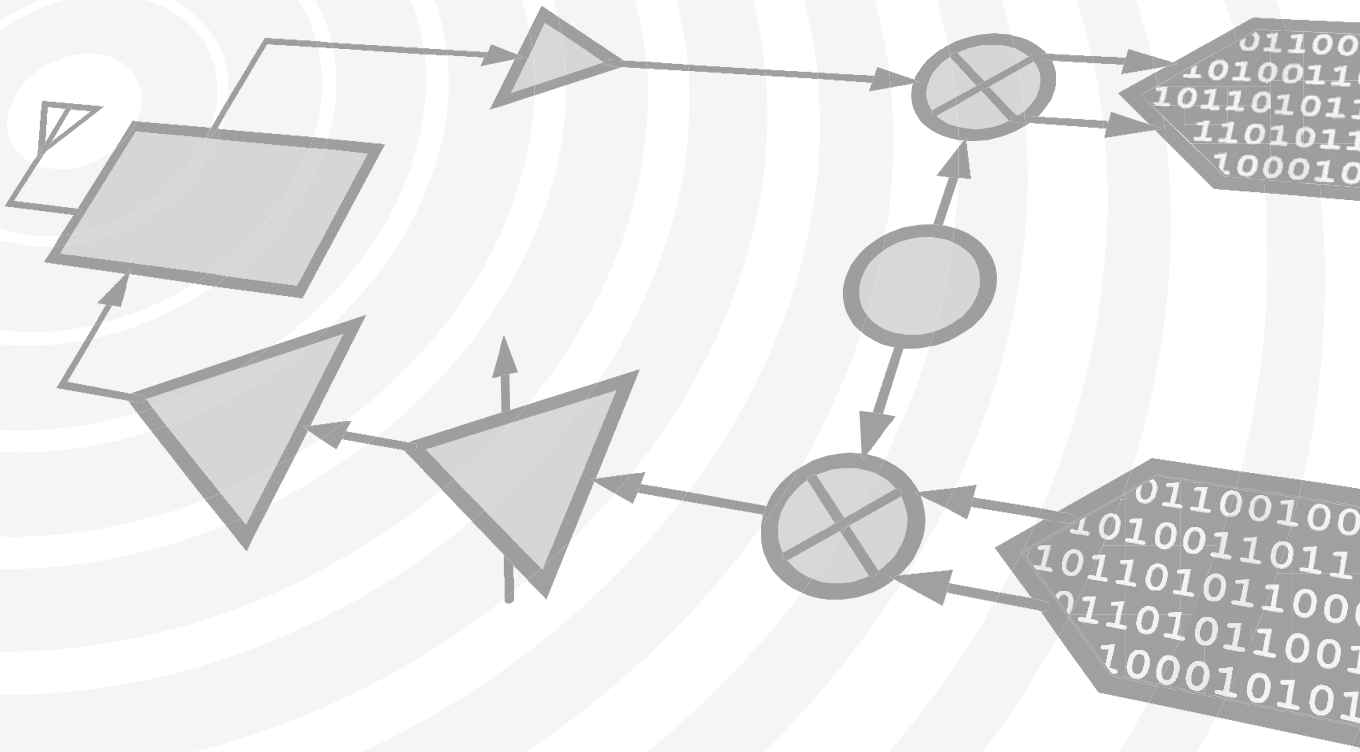

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HMC349AMS8G / 349AMS8GE

v01.0214

HIGH ISOLATION SPDT NON-REFLECTIVE SWITCH, DC - 4 GHz

Typical Applications

The HMC349AMS8G / 349AMS8GE is ideal for:

- Basestation Infrastructure
- MMDS & 3.5 GHz WLL
- CATV/CMTS
- Test Instrumentation

Features

High Isolation: 70 dB @ 1 GHz
57 dB @ 2 GHz

Single Positive Control: 0/+5V

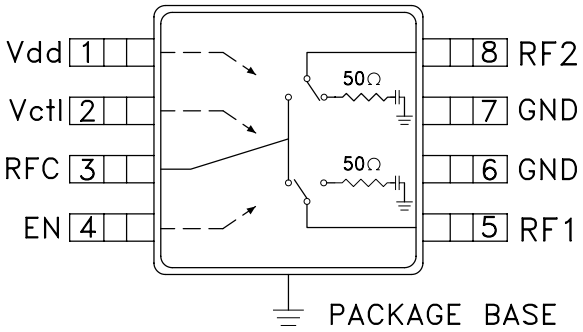
+52 dBm Input IP3

Non-Reflective Design

All Off State

Ultra Small MS8G SMT Package: 14.8 mm^2

Functional Diagram



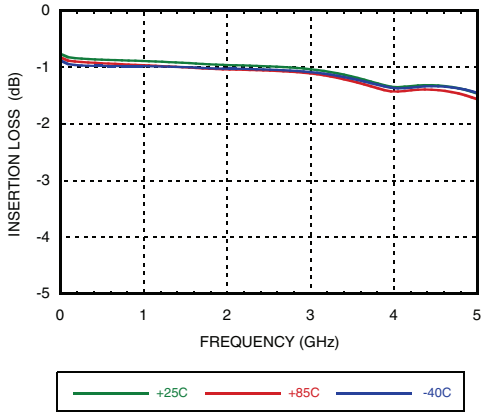
General Description

The HMC349AMS8G & HMC349AMS8GE are high isolation non-reflective DC to 4 GHz GaAs MESFET SPDT switches in low cost 8 lead MSOP8G surface mount packages with exposed ground paddles. The switch is ideal for cellular/PCS/3G basestation applications yielding 50 to 60 dB isolation, low 0.8 dB insertion loss and +52 dBm input IP3. Power handling is excellent up through the 3.5 GHz WLL band with the switch offering a P1dB compression point of +34 dBm. On-chip circuitry allows a single positive voltage control of 0/+5 Volts at very low DC currents. An enable input (EN) set to logic high will put the switch in an "all off" state.

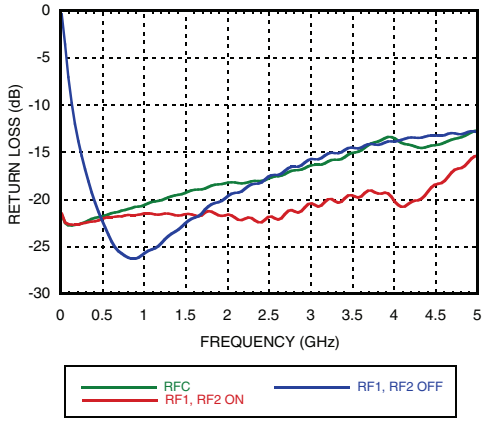
Electrical Specifications, T_A = +25° C, Vctl = 0/+5 Vdc, Vdd = +5 Vdc, 50 Ohm System

Parameter	Frequency	Min.	Typ.	Max.	Units
Insertion Loss	DC - 1.0 GHz DC - 2.0 GHz DC - 3.0 GHz DC - 4.0 GHz		0.8 0.9 1.2 1.8	1.1 1.2 1.5 2.1	dB dB dB dB
Isolation (RFC to RF1/RF2)	DC - 1.0 GHz DC - 2.0 GHz DC - 3.0 GHz DC - 4.0 GHz	60 54 45 42	70 57 50 47		dB dB dB dB
Return Loss (On State)	DC - 1.0 GHz DC - 2.0 GHz DC - 3.0 GHz DC - 4.0 GHz		23 22 20 18		dB dB dB dB
Return Loss (Off State)	0.5 - 2.0 GHz 0.5 - 3.0 GHz 0.5 - 4.0 GHz		22 17 14		dB dB dB
Input Power for 1 dB Compression	0.25 - 4.0 GHz	30	34		dBm
Input Third Order Intercept (Two-Tone Input Power = +10 dBm Each Tone)	0.25 - 1.0 GHz 1.0 - 2.0 GHz 2.0 - 3.0 GHz 3.0 - 4.0 GHz		53 54 53 52		dBm dBm dBm dBm
Switching Speed tRISE, tFALL (10/90% RF) tON, tOFF (50% CTL to 10/90% RF)	DC - 4.0 GHz		 60 160		 ns ns

Insertion Loss

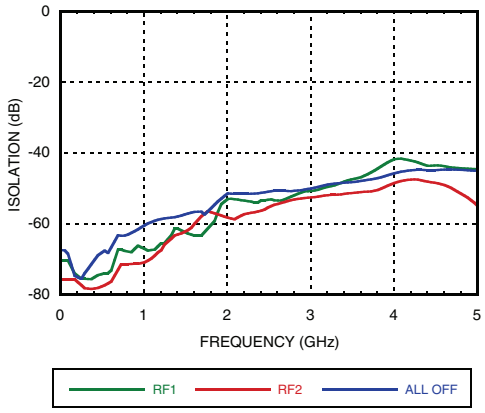


Return Loss

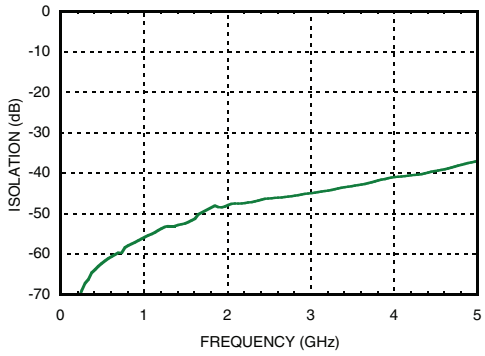


Note: RFC is reflective in "all off" state.

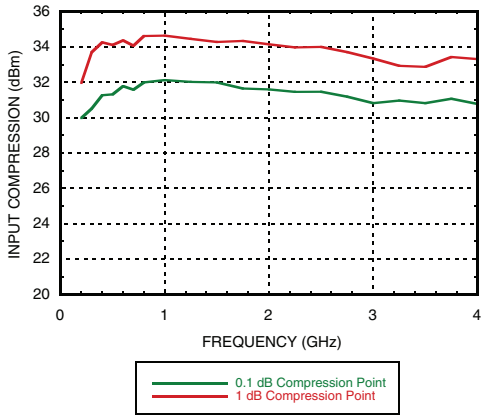
Isolation Between Ports RFC and RF1 / RF2



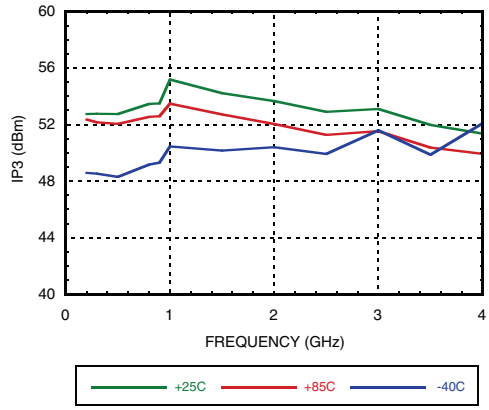
Isolation Between Ports RF1 and RF2



0.1 and 1 dB Input Compression Point



Input Third Order Intercept Point



HMC349AMS8G / 349AMS8GE

HIGH ISOLATION SPDT NON-REFLECTIVE SWITCH, DC - 4 GHz

Absolute Maximum Ratings

RF Input Power (Vctl = 0V/+5V) (0.25 - 4 GHz) Through Path Termination Path	 33.6 dBm 26.5 dBm
Supply Voltage Range (Vdd)	+7 Vdc
Control Voltage Range (Vctl)	-1V to Vdd +1V
Hot Switch Power Level (Vdd = +5V)	+30 dBm
Channel Temperature	150 °C
Continuous Pdiss (T = 85 °C) (derate 17.6 mW/°C for through path, 8.6 mW/°C for temination path above 85 °C) Through Path Termination Path	 0.969 W 0.451 W
Thermal Resistance Through Path Termination Path	 67.1 °C/W 144.2 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 1A

Bias Voltage & Current

Vdd Range = +5.0 Vdc ± 10%		
Vdd (Vdc)	Idd (Typ.) (mA)	Idd (Max.) (mA)
+5.0	1.2	3.5

TTL/CMOS Control Voltages

State	Bias Condition
Low	0 to +0.8 Vdc @ <1 µA Typical
High	+2.0 to +5.0 Vdc @ 40 µA Typical

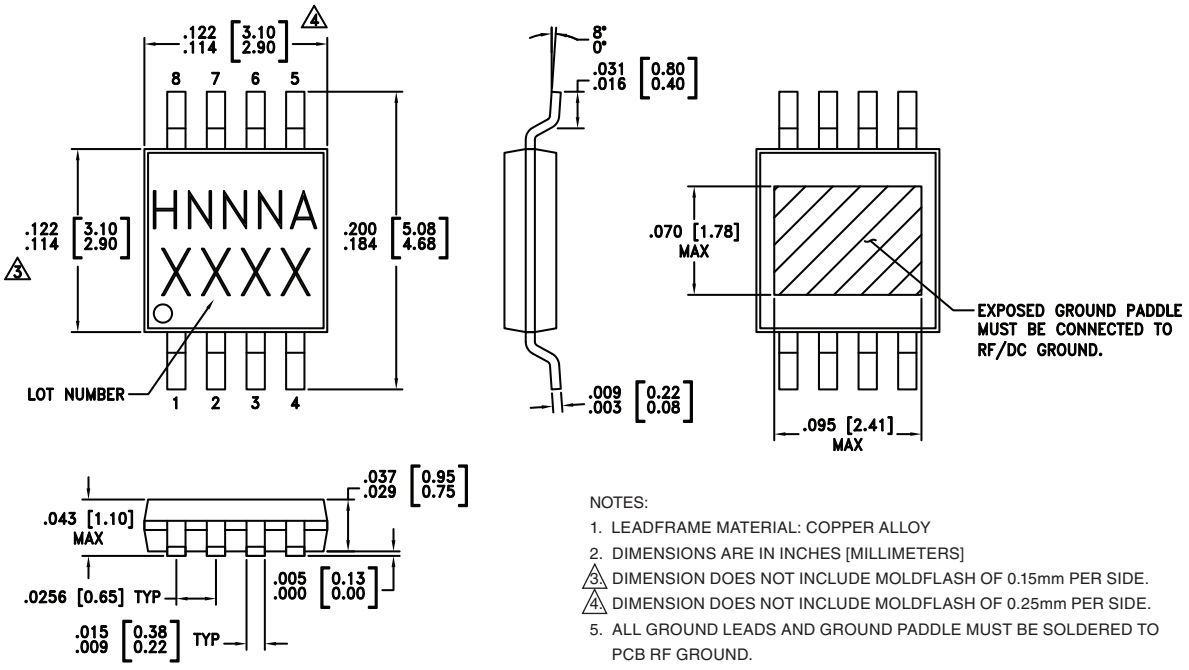
Truth Table

Control Input		Signal Path State	
Vctl	EN	RFC - RF1	RFC - RF2
Low	Low	OFF	ON
High	Low	ON	OFF
Low	High	OFF	OFF
High	High	OFF	OFF

Note: DC blocking capacitors are required at ports RFC, RF1 and RF2. Their value will determine the lowest transmission frequency.

ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Outline Drawing



NOTES:

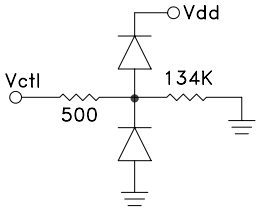
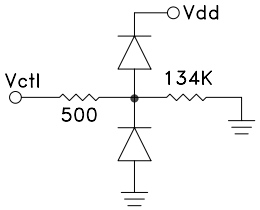
1. LEADFRAME MATERIAL: COPPER ALLOY
2. DIMENSIONS ARE IN INCHES [MILLIMETERS]
3. DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15mm PER SIDE.
4. DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25mm PER SIDE.
5. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.

Package Information

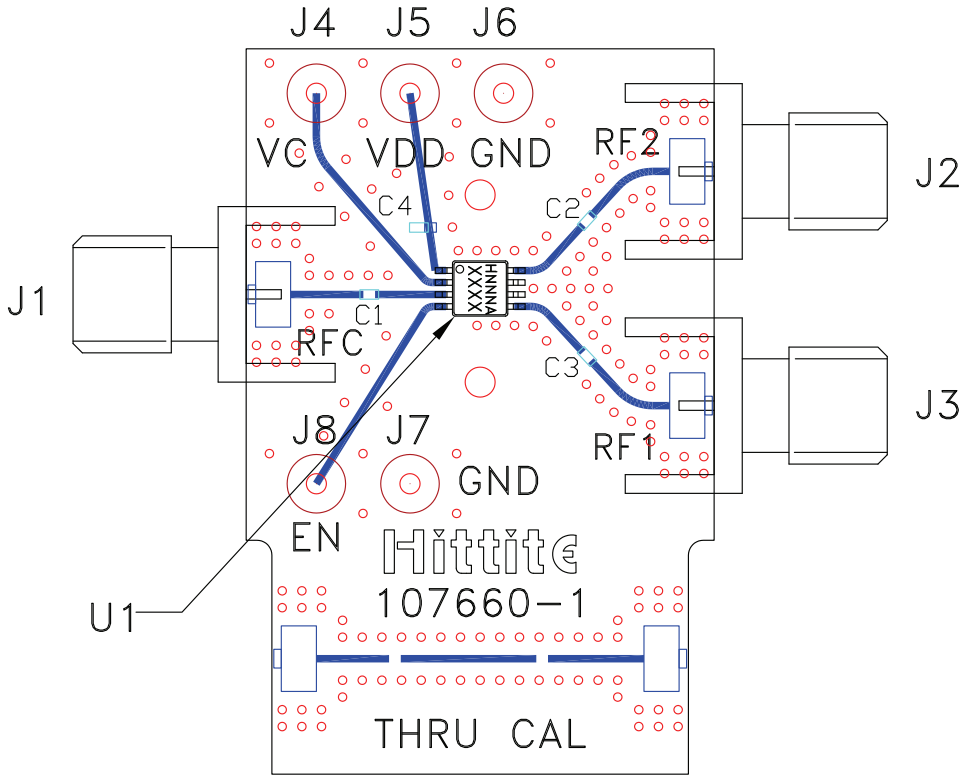
Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [3]
HMC349AMS8G	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 [1]	H349A XXXX
HMC349AMS8GE	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 [2]	H349A XXXX

[1] Max peak reflow temperature of 235 °C
[2] Max peak reflow temperature of 260 °C
[3] 4-Digit lot number XXXX

Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1	Vdd	Supply Voltage.	
2	Vctl	Control input. See truth and control voltage tables.	
3, 5, 8	RFC, RF1, RF2	These pins are DC coupled and matched to 50 Ohms. Blocking capacitors are required.	
4	EN	Enable. See truth and control voltage tables.	
6, 7	GND	Package bottom must also be connected to PCB RF ground.	

Evaluation PCB



List of Materials for Evaluation PCB 107662 - HMC349AMS8G [1]

Item	Description
J1 - J3	PCB Mount SMA RF Connector
J4 - J8	DC Pin
C1 - C3	100 pF Capacitor, 0402 Pkg.
U1	HMC349AMS8G / 349AMS8GE SPDT Switch
PCB [2]	107660 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should be generated with proper RF circuit design techniques. Signal lines at the RF port should have 50 Ohm impedance and the package ground leads and backside ground slug should be connected directly to the ground plane similar to that shown above. The evaluation circuit board shown above is available from Hittite Microwave Corporation upon request.

Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001
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